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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I ² C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, POR, PWM, WDT
Number of I/O	27
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	8K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 10x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-UFQFN Exposed Pad
Supplier Device Package	32-UFQFPN (5x5)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l051k8u7tr

Interconnect source	Interconnect destination	Interconnect action	Run	Sleep	Low- power run	Low- power sleep	Stop
RTC	TIM21	Timer triggered by Auto wake-up	Y	Υ	Y	Y	-
RIC	LPTIM	Timer triggered by RTC event	Y	Y	Y	Y	Υ
All clock source	TIMx	Clock source used as input channel for RC measurement and trimming	Υ	Y	Y	Y	-
	TIMx	Timer input channel and trigger	Y	Υ	Y	Υ	-
GPIO	LPTIM	Timer input channel and trigger	Y	Y	Y	Y	Y
	ADC	Conversion trigger	Υ	Υ	Y	Y	-

Table 6. STM32L0xx peripherals interconnect matrix (continued)

3.3 ARM® Cortex®-M0+ core with MPU

The Cortex-M0+ processor is an entry-level 32-bit ARM Cortex processor designed for a broad range of embedded applications. It offers significant benefits to developers, including:

- a simple architecture that is easy to learn and program
- ultra-low power, energy-efficient operation
- excellent code density
- deterministic, high-performance interrupt handling
- upward compatibility with Cortex-M processor family
- platform security robustness, with integrated Memory Protection Unit (MPU).

The Cortex-M0+ processor is built on a highly area and power optimized 32-bit processor core, with a 2-stage pipeline Von Neumann architecture. The processor delivers exceptional energy efficiency through a small but powerful instruction set and extensively optimized design, providing high-end processing hardware including a single-cycle multiplier.

The Cortex-M0+ processor provides the exceptional performance expected of a modern 32-bit architecture, with a higher code density than other 8-bit and 16-bit microcontrollers.

Owing to its embedded ARM core, the STM32L051x6/8 are compatible with all ARM tools and software.

internal reference voltage (V_{REFINT}) in Stop mode. The device remains in reset mode when V_{DD} is below a specified threshold, $V_{POR/PDR}$ or V_{BOR} , without the need for any external reset circuit.

Note:

The start-up time at power-on is typically 3.3 ms when BOR is active at power-up, the start-up time at power-on can be decreased down to 1 ms typically for devices with BOR inactive at power-up.

The devices feature an embedded programmable voltage detector (PVD) that monitors the $V_{DD/VDDA}$ power supply and compares it to the V_{PVD} threshold. This PVD offers 7 different levels between 1.85 V and 3.05 V, chosen by software, with a step around 200 mV. An interrupt can be generated when $V_{DD/VDDA}$ drops below the V_{PVD} threshold and/or when $V_{DD/VDDA}$ is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.4.3 Voltage regulator

The regulator has three operation modes: main (MR), low power (LPR) and power down.

- MR is used in Run mode (nominal regulation)
- LPR is used in the Low-power run, Low-power sleep and Stop modes
- Power down is used in Standby mode. The regulator output is high impedance, the kernel circuitry is powered down, inducing zero consumption but the contents of the registers and RAM are lost except for the standby circuitry (wakeup logic, IWDG, RTC, LSI, LSE crystal 32 KHz oscillator, RCC_CSR).

3.5 Clock management

The clock controller distributes the clocks coming from different oscillators to the core and the peripherals. It also manages clock gating for low-power modes and ensures clock robustness. It features:

Clock prescaler

To get the best trade-off between speed and current consumption, the clock frequency to the CPU and peripherals can be adjusted by a programmable prescaler.

Safe clock switching

Clock sources can be changed safely on the fly in Run mode through a configuration register.

Clock management

To reduce power consumption, the clock controller can stop the clock to the core, individual peripherals or memory.

System clock source

Three different clock sources can be used to drive the master clock SYSCLK:

- 1-25 MHz high-speed external crystal (HSE), that can supply a PLL
- 16 MHz high-speed internal RC oscillator (HSI), trimmable by software, that can supply a PLLMultispeed internal RC oscillator (MSI), trimmable by software, able to generate 7 frequencies (65 kHz, 131 kHz, 262 kHz, 524 kHz, 1.05 MHz, 2.1 MHz, 4.2 MHz). When a 32.768 kHz clock source is available in the system (LSE), the MSI frequency can be trimmed by software down to a ±0.5% accuracy.

Auxiliary clock source

Two ultra-low-power clock sources that can be used to drive the real-time clock:



3.8 Memories

The STM32L051x6/8 devices have the following features:

- 8 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states. With the enhanced bus matrix, operating the RAM does not lead to any performance penalty during accesses to the system bus (AHB and APB buses).
- The non-volatile memory is divided into three arrays:
 - 32 or 64 Kbytes of embedded Flash program memory
 - 2 Kbytes of data EEPROM
 - Information block containing 32 user and factory options bytes plus 4 Kbytes of system memory

The user options bytes are used to write-protect or read-out protect the memory (with 4 Kbyte granularity) and/or readout-protect the whole memory with the following options:

- Level 0: no protection
- Level 1: memory readout protected.
 - The Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
- **Level 2**: chip readout protected, debug features (Cortex-M0+ serial wire) and boot in RAM selection disabled (debugline fuse)

The firewall protects parts of code/data from access by the rest of the code that is executed outside of the protected area. The granularity of the protected code segment or the non-volatile data segment is 256 bytes (Flash memory or EEPROM) against 64 bytes for the volatile data segment (RAM).

The whole non-volatile memory embeds the error correction code (ECC) feature.

3.9 Boot modes

At startup, BOOT0 pin and nBOOT1 option bit are used to select one of three boot options:

- Boot from Flash memory
- Boot from System memory
- · Boot from embedded RAM

The boot loader is located in System memory. It is used to reprogram the Flash memory by using SPI1(PA4, PA5, PA6, PA7) or SPI2 (PB12, PB13, PB14, PB15), USART1(PA9, PA10) or USART2(PA2, PA3). See STM32™ microcontroller system memory boot mode AN2606 for details.

To improve the accuracy of the temperature sensor measurement, each device is individually factory-calibrated by ST. The temperature sensor factory calibration data are stored by ST in the system memory area, accessible in read-only mode.

Calibration value name	Description	Memory address		
TSENSE_CAL1	TS ADC raw data acquired at temperature of 30 °C, V _{DDA} = 3 V	0x1FF8 007A - 0x1FF8 007B		
TSENSE_CAL2	TS ADC raw data acquired at temperature of 130 °C V _{DDA} = 3 V	0x1FF8 007E - 0x1FF8 007F		

Table 7. Temperature sensor calibration values

3.12.1 Internal voltage reference (V_{REFINT})

The internal voltage reference (V_{REFINT}) provides a stable (bandgap) voltage output for the ADC and Comparators. V_{REFINT} is internally connected to the ADC_IN17 input channel. It enables accurate monitoring of the V_{DD} value (when no external voltage, V_{REF+} , is available for ADC). The precise voltage of V_{REFINT} is individually measured for each part by ST during production test and stored in the system memory area. It is accessible in read-only mode.

Table 8. Internal voltage reference measured values

Calibration value name	Description	Memory address
VREFINT_CAL	Raw data acquired at temperature of 25 °C V _{DDA} = 3 V	0x1FF8 0078 - 0x1FF8 0079

3.13 Ultra-low-power comparators and reference voltage

The STM32L051x6/8 embed two comparators sharing the same current bias and reference voltage. The reference voltage can be internal or external (coming from an I/O).

- One comparator with ultra low consumption
- One comparator with rail-to-rail inputs, fast or slow mode.
- The threshold can be one of the following:
 - External I/O pins
 - Internal reference voltage (V_{REFINT})
 - submultiple of Internal reference voltage(1/4, 1/2, 3/4) for the rail to rail comparator.

Both comparators can wake up the devices from Stop mode, and be combined into a window comparator.

The internal reference voltage is available externally via a low-power / low-current output buffer (driving current capability of 1 µA typical).

3.14 System configuration controller

The system configuration controller provides the capability to remap some alternate functions on different I/O ports.

The highly flexible routing interface allows the application firmware to control the routing of different I/Os to the TIM2, TIM21, TIM22 and LPTIM timer input captures. It also controls the routing of internal analog signals to ADC, COMP1 and COMP2 and the internal reference voltage V_{REFINT}.

3.15 Timers and watchdogs

The ultra-low-power STM32L051x6/8 devices include three general-purpose timers, one low-power timer (LPTIM), one basic timer, two watchdog timers and the SysTick timer.

Table 9 compares the features of the general-purpose and basic timers.

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM2	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM21, TIM22	16-bit	Up, down, up/down	Any integer between 1 and 65536	No	2	No
TIM6	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

Table 9. Timer feature comparison

3.15.1 General-purpose timers (TIM2, TIM21 and TIM22)

There are three synchronizable general-purpose timers embedded in the STM32L051x6/8 devices (see *Table 9* for differences).

TIM₂

TIM2 is based on 16-bit auto-reload up/down counter. It includes a 16-bit prescaler. It features four independent channels each for input capture/output compare, PWM or one-pulse mode output.

The TIM2 general-purpose timers can work together or with the TIM21 and TIM22 general-purpose timers via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs.

TIM2 has independent DMA request generation.

This timer is capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

TIM21 and TIM22

TIM21 and TIM22 are based on a 16-bit auto-reload up/down counter. They include a 16-bit prescaler. They have two independent channels for input capture/output compare, PWM or



Table 15. STM32L051x6/8 pin definitions (continued)

		Pin Nu	umber				-			,	
LQFP64	TFBGA64	LQFP48	WLCSP36 ⁽¹⁾	LQFP32	UFQFPN32	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
5	C1	5	-	-	-	PH0-OSC_IN (PH0)	I/O	TC	-	-	OSC_IN
6	D1	6	-	-	-	PH1- OSC_OUT (PH1)	I/O	тс	1	-	OSC_OUT
7	E1	7	C6	4	4	NRST	I/O	RST	-	-	-
8	E3	-	-	-	-	PC0	I/O	FT	-	LPTIM1_IN1, EVENTOUT	ADC_IN10
9	E2	-	-	-	-	PC1	I/O	FT	-	LPTIM1_OUT, EVENTOUT	ADC_IN11
10	F2	-	-	-	-	PC2	I/O	FT	-	LPTIM1_IN2, SPI2_MISO/I2S2_M CK	ADC_IN12
11	-	-	-	ı	-	PC3	I/O	FT	1	LPTIM1_ETR, SPI2_MOSI/I2S2_SD	ADC_IN13
12	F1	8	-	-	-	VSSA	S		-	-	-
-	G1	-	E6	ı	ı	VREF+	S		1	-	-
13	H1	9	D5	5	5	VDDA	S		ı	-	-
14	G2	10	D4	6	6	PA0	I/O	TC	1	TIM2_CH1, USART2_CTS, TIM2_ETR, COMP1_OUT	COMP1_INM6, ADC_IN0, RTC_TAMP2/WKU P1
15	H2	11	F6	7	7	PA1	I/O	FT	1	EVENTOUT, TIM2_CH2, USART2_RTS_DE, TIM21_ETR	COMP1_INP, ADC_IN1
16	F3	12	E5	8	8	PA2	I/O	FT	-	TIM21_CH1, TIM2_CH3, USART2_TX, COMP2_OUT	COMP2_INM6, ADC_IN2
17	G3	13	F5	9	9	PA3	I/O	FT	-	TIM21_CH2, TIM2_CH4, USART2_RX	COMP2_INP, ADC_IN3
18	C2	-	-	-	-	VSS	S		-	-	-

Table 15. STM32L051x6/8 pin definitions (continued)

		Pin N	ımber								
LQFP64	TFBGA64	LQFP48	WLCSP36 ⁽¹⁾	LQFP32	UFQFPN32	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
19	D2	-	-	-	-	VDD	S		-	-	-
20	НЗ	14	E4	10	10	PA4	I/O	TC		SPI1_NSS, USART2_CK, TIM22_ETR	COMP1_INM4, COMP2_INM4, ADC_IN4
21	F4	15	F4	11	11	PA5	I/O	TC	ı	SPI1_SCK, TIM2_ETR, TIM2_CH1	COMP1_INM5, COMP2_INM5, ADC_IN5
22	G4	16	E3	12	12	PA6	I/O	FT	-	SPI1_MISO, LPUART1_CTS, TIM22_CH1, EVENTOUT, COMP1_OUT	ADC_IN6
23	H4	17	F3	13	13	PA7	I/O	FT	1	SPI1_MOSI, TIM22_CH2, EVENTOUT, COMP2_OUT	ADC_IN7
24	H5	ı	1	-	-	PC4	I/O	FT	ı	EVENTOUT, LPUART1_TX	ADC_IN14
25	H6	ı	ı	-	-	PC5	I/O	FT	-	LPUART1_RX,	ADC_IN15
26	F5	18	D3	14	14	PB0	I/O	FT	i	EVENTOUT	ADC_IN8, VREF_OUT
27	G5	19	C3	15	15	PB1	I/O	FT	i	LPUART1_RTS_DE	ADC_IN9, VREF_OUT
28	G6	20	F2	-	16	PB2	I/O	FT	-	LPTIM1_OUT	-
29	G7	21	E2	-	-	PB10	I/O	FT	-	TIM2_CH3, LPUART1_TX, SPI2_SCK, I2C2_SCL	-
30	H7	22	D2	-	-	PB11	I/O	FT	-	EVENTOUT, TIM2_CH4, LPUART1_RX, I2C2_SDA	-
31	D6	23	1	16	-	VSS	S	-	-	-	-
32	E6	24	F1	17	17	VDD	S	-	-	-	-

Table 15. STM32L051x6/8 pin definitions (continued)

		Pin Nu	umber		- 101 0		, p			is (continued)		
LQFP64	TFBGA64	LQFP48	WLCSP36 ⁽¹⁾	LQFP32	UFQFPN32	Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions	
48	E5	36	-	-	-	VDDIO2	S		1	-	-	
49	A7	37	B2	24	24	PA14	I/O	FT	-	SWCLK, USART2_TX		
50	A6	38	A2	25	25	PA15	I/O	FT	1	SPI1_NSS, TIM2_ETR, EVENTOUT, USART2_RX, TIM2_CH1	,	
51	В7	-	-	-	-	PC10	I/O	FT	ı	LPUART1_TX	-	
52	В6	-	-	-	-	PC11	I/O	FT	ı	LPUART1_RX	-	
53	C5	-	-	-	-	PC12	I/O	FT	-	-	-	
54	B5	-	-	-	-	PD2	I/O	FT	-	LPUART1_RTS_DE	-	
55	A5	39	В3	26	26	PB3	I/O	FT	1	SPI1_SCK, TIM2_CH2, EVENTOUT	COMP2_INN	
56	A4	40	A3	27	27	PB4	I/O	FT	1	SPI1_MISO, EVENTOUT, TIM22_CH1	COMP2_INP	
57	C4	41	C4	28	28	PB5	I/O	FT	-	SPI1_MOSI, LPTIM1_IN1, I2C1_SMBA, TIM22_CH2	COMP2_INP	
58	D3	42	B4	29	29	PB6	I/O	FTf	i	USART1_TX, I2C1_SCL, LPTIM1_ETR	COMP2_INP	
59	C3	43	A4	30	30	PB7	I/O	FTf	i	USART1_RX, I2C1_SDA, LPTIM1_IN2	COMP2_INP, PVD_IN	
60	B4	44	C5	31	31	воото	В		-	-	-	
61	ВЗ	45	B5	-	32	PB8	I/O	FTf	-	I2C1_SCL	-	
62	А3	46	-	-	-	PB9	I/O	FTf	-	EVENTOUT, I2C1_SDA, SPI2_NSS/I2S2_WS	-	

	Table 16. Alternate function port A									
		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	
Po	ort	SPI1/TIM21/SYS_A F/EVENTOUT/	-	TIM2/ EVENTOUT/	EVENTOUT	USART1/2/3	TIM2/21/22	EVENTOUT	COMP1/2	
	PA0	-	-	TIM2_CH1	-	USART2_CTS	TIM2_ETR	-	COMP1_OUT	
	PA1	EVENTOUT	-	TIM2_CH2	-	USART2_RTS_ DE	TIM21_ETR	-	-	
	PA2	TIM21_CH1	-	TIM2_CH3	-	USART2_TX	-	-	COMP2_OUT	
	PA3	TIM21_CH2	-	TIM2_CH4	-	USART2_RX	-	-	-	
	PA4	SPI1_NSS	-	-	-	USART2_CK	TIM22_ETR	-	-	
	PA5	SPI1_SCK	-	TIM2_ETR	-	-	TIM2_CH1	-	-	
	PA6	SPI1_MISO	-	-	-	LPUART1_CTS	TIM22_CH1	EVENTOUT	COMP1_OUT	
Port A	PA7	SPI1_MOSI	-	-	-	-	TIM22_CH2	EVENTOUT	COMP2_OUT	
POILA	PA8	МСО	-	-	EVENTOUT	USART1_CK	-	-	-	
	PA9	MCO	-	-	-	USART1_TX	-	-	-	
	PA10	-	-	-	-	USART1_RX	-	-	-	
	PA11	SPI1_MISO	-	EVENTOUT	-	USART1_CTS	-	-	COMP1_OUT	
	PA12	SPI1_MOSI	-	EVENTOUT	-	USART1_RTS_ DE	-	-	COMP2_OUT	
	PA13	SWDIO	-	-	-	-	-	-	-	
	PA14	SWCLK	-	-	-	USART2_TX	-	-	-	
	PA15	SPI1_NSS	-	TIM2_ETR	EVENTOUT	USART2_RX	TIM2_CH1	-	-	



6.1.6 Power supply scheme

Standby-power circuitry (OSC32,RTC,Wake-up logic, RTC backup registers) Ю GP I/Os Logic Kernel logic (CPU, Digital & Memories) Regulator N × 100 nF $+ 1 \times 10 \mu F$ V_{DDA} V_{DDA} V_{REF+} 100 nF Analog: RC,PLL,COMP, + 1 µF ADC V_{REF} V_{SSA} MSv34740V1

Figure 12. Power supply scheme

6.1.7 Current consumption measurement

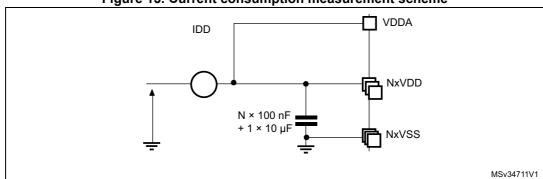


Figure 13. Current consumption measurement scheme

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in the following tables. The MCU is placed under the following conditions:

- \bullet $\,$ all I/O pins are in input mode with a static value at V_{DD} or V_{SS} (no load)
- all peripherals are disabled unless otherwise mentioned
- the given value is calculated by measuring the current consumption
 - with all peripherals clocked OFF
 - with only one peripheral clocked on

Table 37. Peripheral current consumption in Run or Sleep mode⁽¹⁾

		Typical	consumption, V	/ _{DD} = 3.0 V, T _A =	25 °C					
Per	ipheral	Range 1, V _{CORE} =1.8 V VOS[1:0] = 01	Range 2, V _{CORE} =1.5 V VOS[1:0] = 10	Range 3, V _{CORE} =1.2 V VOS[1:0] = 11	Low-power sleep and run	Unit				
	I2C1	11	9.5	7.5	9					
	I2C2	4	3.5	3	2.5					
	LPTIM1	10	8.5	6.5	8					
	LPUART1	8	6.5	5.5	6					
APB1	SPI2	9	4.5	3.5	4	μΑ/MHz (f _{HCLK})				
	USART2	14.5	12	9.5	11	('HCLK)				
	TIM2	10.5	8.5	7	9					
	TIM6	3.5	3	2.5	2					
	WWDG	3	2	2	2					
	ADC1 ⁽²⁾	5.5	5	3.5	4					
	SPI1	4	3	3	2.5					
	USART1	14.5	11.5	9.5	12					
APB2	TIM21	7.5	6	5	5.5	μΑ/MHz				
APB2	TIM22	7	6	5	6	(f _{HCLK})				
	FIREWALL	1.5	1	1	0.5					
	DBGMCU	1.5	1	1	0.5					
	SYSCFG	2.5	2	2	1.5					
	GPIOA	3.5	3	2.5	2.5					
Cortex-	GPIOB	3.5	2.5	2	2.5	μΑ/MHz				
M0+ core I/O port	GPIOC	8.5	6.5	5.5	7	(f _{HCLK})				
	GPIOD	1	0.5	0.5	0.5					
	CRC	1.5	1	1	1					
AHB	FLASH	0(3)	0(3)	0(3)	0 ⁽³⁾	μΑ/MHz (f _{HCLK})				
	DMA1	10	8	6.5	8.5	('HCLK)				



Table 46. MSI oscillator characteristics (continued)

Symbol	Parameter	Condition	Тур	Max	Unit	
		MSI range 0	0.75	-		
		MSI range 1	1	-		
		MSI range 2	1.5	-		
I _{DD(MSI)} ⁽²⁾	MSI oscillator power consumption	MSI range 3	2.5	-	μΑ	
		MSI range 4	4.5	-		
		MSI range 5	8	-		
		MSI range 6	15	-		
		MSI range 0	30	-		
		MSI range 1	20	-		
		MSI range 2	15	-		
		MSI range 3	10	-		
	MCI agaillatar startus tima	MSI range 4	6	-	μs	
t _{SU(MSI)}	MSI oscillator startup time	MSI range 5	5	-		
		MSI range 6, Voltage range 1 and 2	3.5	-		
		MSI range 6, Voltage range 3	5	-		
		MSI range 0	-	40		
		MSI range 1	-	20	-	
		MSI range 2	-	10		
		MSI range 3	-	4		
t _{STAB(MSI)} ⁽²⁾	MSI oscillator stabilization time	MSI range 4	-	2.5	μs	
STAB(MSI)	Wor oscillator stabilization time	MSI range 5	-	2	μο	
		MSI range 6, Voltage range 1 and 2	-	2		
		MSI range 3, Voltage range 3	-	3		
f	MSI oscillator frequency overshoot	Any range to range 5	-	4		
f _{OVER(MSI)}	ivior oscillator frequency overshoot	Any range to range 6	-	6	MHz	

^{1.} This is a deviation for an individual part, once the initial frequency has been measured.

^{2.} Guaranteed by characterization results.

6.3.11 Electrical sensitivity characteristics

Based on three different tests (ESD, LU) using specific measurement methods, the device is stressed in order to determine its performance in terms of electrical sensitivity.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pins). This test conforms to the ANSI/JEDEC standard.

Table 53. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value ⁽¹⁾	Unit
V _{ESD(HBM)}	Electrostatic discharge voltage (human body model)	T _A = +25 °C, conforming to ANSI/JEDEC JS-001	2	2000	V
V _{ESD(CDM)}	Electrostatic discharge voltage (charge device model)	T _A = +25 °C, conforming to ANSI/ESD STM5.3.1.	C4	500	V

^{1.} Guaranteed by characterization results.

Static latch-up

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin
- A current injection is applied to each input, output and configurable I/O pin

These tests are compliant with EIA/JESD 78A IC latch-up standard.

Table 54. Electrical sensitivities

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T _A = +125 °C conforming to JESD78A	II level A

Table 60. ADC characteristics (continued)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{AIN} ⁽³⁾	External input impedance	See Equation 1 and Table 61 for details	-	-	50	kΩ
R _{ADC} (3)(4)	Sampling switch resistance	-	-	-	1	kΩ
C _{ADC} ⁽³⁾	Internal sample and hold capacitor	-	-	-	8	pF
t _{CAL} (3)(5)	Calibration time	f _{ADC} = 16 MHz		5.2		μs
CAL, ,, ,	Calibration time	-		83		1/f _{ADC}
		ADC clock = HSI16	1.5 ADC cycles + 2 f _{PCLK} cycles	ı	1.5 ADC cycles + 3 f _{PCLK} cycles	-
W _{LATENCY} ⁽⁶⁾	ADC_DR register write latency	ADC clock = PCLK/2	-	4.5	-	f _{PCLK} cycle
		ADC clock = PCLK/4	-	8.5	-	f _{PCLK} cycle
	Trigger conversion latency	$f_{ADC} = f_{PCLK}/2 = 16 \text{ MHz}$	0.266			μs
		$f_{ADC} = f_{PCLK}/2$	8.5			1/f _{PCLK}
t _{latr} (3)		$f_{ADC} = f_{PCLK}/4 = 8 \text{ MHz}$	0.516			μs
		$f_{ADC} = f_{PCLK}/4$	16.5			1/f _{PCLK}
		$f_{ADC} = f_{HSI16} = 16 \text{ MHz}$	0.252	-	0.260	μs
Jitter _{ADC}	ADC jitter on trigger conversion	f _{ADC} = f _{HSI16}	-	1	-	1/f _{HSI16}
ts ⁽³⁾	Sampling time	f _{ADC} = 16 MHz	0.093	-	10.03	μs
ıs. ,	Sampling time	-	1.5	-	160.5	1/f _{ADC}
t _{UP_LDO} (3)(5) Internal LDO power-up time		-	-	-	10	μs
t _{STAB} ⁽³⁾⁽⁵⁾	ADC stabilization time	-	14			1/f _{ADC}
t _{ConV} ⁽³⁾	Total conversion time	f _{ADC} = 16 MHz, 12-bit resolution	0.875	-	10.81	μs
^L ConV` ′	(including sampling time)	12-bit resolution	14 to 173 (t _S for sampling +12.5 for successive approximation)		1/f _{ADC}	

^{1.} V_{DDA} minimum value can be decreased in specific temperature conditions. Refer to *Table 61: RAIN max for fADC = 16 MHz*.

^{2.} A current consumption proportional to the APB clock frequency has to be added (see *Table 37: Peripheral current consumption in Run or Sleep mode*).

^{3.} Guaranteed by design.

Standard channels have an extra protection resistance which depends on supply voltage. Refer to Table 61: RAIN max for fADC = 16 MHz.

^{5.} This parameter only includes the ADC timing. It does not take into account register access latency.

^{6.} This parameter specifies the latency to transfer the conversion result into the ADC_DR register. EOC bit is set to indicate the conversion is complete and has the same latency.

6.3.17 Comparators

Table 65. Comparator 1 characteristics

Symbol	Parameter	Conditions	Min ⁽¹⁾	Тур	Max ⁽¹⁾	Unit	
V_{DDA}	Analog supply voltage	-	1.65		3.6	V	
R _{400K}	R _{400K} value	-	-	400	-	kΩ	
R _{10K}	R _{10K} value	-	-	10	-	K22	
V _{IN}	Comparator 1 input voltage range	-	0.6	-	V_{DDA}	V	
t _{START}	Comparator startup time	-	-	7	10	1	
td	Propagation delay ⁽²⁾	-	-	3	10	μs	
Voffset	Comparator offset	-	-	±3	±10	mV	
d _{Voffset} /dt	Comparator offset variation in worst voltage stress conditions	$\begin{split} V_{DDA} &= 3.6 \text{ V}, V_{IN+} = 0 \text{ V}, \\ V_{IN-} &= V_{REFINT}, T_A = 25 \ ^{\circ}\text{C} \end{split}$	0	1.5	10	mV/1000 h	
I _{COMP1}	Current consumption ⁽³⁾	-	-	160	260	nA	

^{1.} Guaranteed by characterization.

Table 66. Comparator 2 characteristics

Symbol	Parameter	Conditions	Min	Тур	Max ⁽¹⁾	Unit
V_{DDA}	Analog supply voltage	-	1.65	-	3.6	V
V _{IN}	Comparator 2 input voltage range	-	0	-	V_{DDA}	V
t	Comparator startup time	Fast mode	-	15	20	
t _{START}	Comparator startup time	Slow mode	-	20	25	
•	Propagation delay ⁽²⁾ in slow mode	1.65 V ≤V _{DDA} ≤2.7 V	-	1.8	3.5	
t _{d slow}	Propagation delay 7 in Slow mode	2.7 V ≤V _{DDA} ≤3.6 V	-	2.5	6	μs
•	Propagation delay ⁽²⁾ in fast mode	1.65 V ≤V _{DDA} ≤2.7 V	-	0.8	2	
t _{d fast}	Fropagation delay Virriast mode	2.7 V ≤V _{DDA} ≤3.6 V	- 1.2 4		4]
V _{offset}	Comparator offset error		-	<u>±4</u>	±20	mV
dThreshold/ dt	Threshold voltage temperature coefficient	$V_{DDA} = 3.3V$, $T_A = 0$ to $50 ^{\circ}$ C, $V_{-} = V_{REFINT}$, $3/4 ^{\circ}$ V_{REFINT} , $1/2 ^{\circ}$ V_{REFINT} , $1/4 ^{\circ}$ V_{REFINT} .	-	15	30	ppm /°C
1	Current consumption ⁽³⁾	Fast mode	-	3.5	5	
I _{COMP2}	Current consumption.	Slow mode	-	0.5	2	μA

^{1.} Guaranteed by characterization results.

^{2.} The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.

^{3.} Comparator consumption only. Internal reference voltage not included.

^{2.} The delay is characterized for 100 mV input step with 10 mV overdrive on the inverting input, the non-inverting input set to the reference.

^{3.} Comparator consumption only. Internal reference voltage (required for comparator operation) is not included.

6.3.18 Timer characteristics

TIM timer characteristics

The parameters given in the *Table 67* are guaranteed by design.

Refer to Section 6.3.13: I/O port characteristics for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

Symbol	Symbol Parameter		Min	Max	Unit		
t	Timer resolution time		1	-	t _{TIMxCLK}		
^t res(TIM)	Timer resolution time	f _{TIMxCLK} = 32 MHz	31.25	-	ns		
f	Timer external clock frequency on CH1 to CH4		0	f _{TIMxCLK} /2	MHz		
f _{EXT}		f _{TIMxCLK} = 32 MHz	0	16	MHz		
Res _{TIM}	Res _{TIM} Timer resolution			16	bit		
	16-bit counter clock period when	-	1	65536	t _{TIMxCLK}		
^t COUNTER	internal clock is selected (timer's prescaler disabled)	f _{TIMxCLK} = 32 MHz	0.0312	2048	μs		
+	Maximum possible count	-	-	65536 × 65536	t _{TIMxCLK}		
t _{MAX_COUNT}	Maximum possible count	f _{TIMxCLK} = 32 MHz	-	134.2	S		

Table 67. TIMx characteristics⁽¹⁾

6.3.19 Communications interfaces

I²C interface characteristics

The I²C interface meets the timings requirements of the I²C-bus specification and user manual rev. 03 for:

- Standard-mode (Sm): with a bit rate up to 100 kbit/s
- Fast-mode (Fm): with a bit rate up to 400 kbit/s
- Fast-mode Plus (Fm+): with a bit rate up to 1 Mbit/s.

The I²C timing requirements are guaranteed by design when the I²C peripheral is properly configured (refer to the reference manual for details). The SDA and SCL I/O requirements are met with the following restrictions: the SDA and SCL I/O pins are not "true" open-drain. When configured as open-drain, the PMOS connected between the I/O pin and VDDIOx is disabled, but is still present. Only FTf I/O pins support Fm+ low level output current maximum requirement (refer to Section 6.3.13: I/O port characteristics for the I2C I/Os characteristics).

All I²C SDA and SCL I/Os embed an analog filter (see *Table 68* for the analog filter characteristics).

^{1.} TIMx is used as a general term to refer to the TIM2, TIM6, TIM21, and TIM22 timers.

SPI characteristics

Unless otherwise specified, the parameters given in the following tables are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 23*.

Refer to Section 6.3.12: I/O current injection characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 70. SPI characteristics in voltage Range 1 (1)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Master mode			16	
	SPI clock frequency	Slave mode receiver	-	-	16	
f _{SCK} 1/t _{c(SCK)}		Slave mode Transmitter 1.71 <v<sub>DD<3.6V</v<sub>	-	-	12 ⁽²⁾	MHz
		Slave mode Transmitter 2.7 <v<sub>DD<3.6V</v<sub>	-	-	16 ⁽²⁾	
Duty _(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
t _{su(NSS)}	NSS setup time	Slave mode, SPI presc = 2	4*Tpclk	-	-	
t _{h(NSS)}	NSS hold time	Slave mode, SPI presc = 2	2*Tpclk	-	-	
t _{w(SCKH)}	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+	
t _{su(MI)}	Data input setup time	Master mode	0	-	-	
t _{su(SI)}	Data input setup time	Slave mode	3	-	-	
t _{h(MI)}	Data input hold time	Master mode	7	-	-	
t _{h(SI)}	Data input noid time	Slave mode	3.5	-	-	ns
t _{a(SO}	Data output access time	Slave mode	15	-	36	
t _{dis(SO)}	Data output disable time	Slave mode	10	-	30	
	Data output valid time	Slave mode 1.65 V <v<sub>DD<3.6 V</v<sub>	-	18	41	
t _{v(SO)}		Slave mode 2.7 V <v<sub>DD<3.6 V</v<sub>	_	18	25	
t _{v(MO)}		Master mode	-	4	7	
t _{h(SO)}	Data output hold time	Slave mode	10	-	-	
t _{h(MO)}	Data output noid time	Master mode	0	-	-	

^{1.} Guaranteed by characterization results.



^{2.} The maximum SPI clock frequency in slave transmitter mode is determined by the sum of $t_{v(SO)}$ and $t_{su(MI)}$ which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having $t_{su(MI)} = 0$ while $\text{Duty}_{(SCK)} = 50\%$.

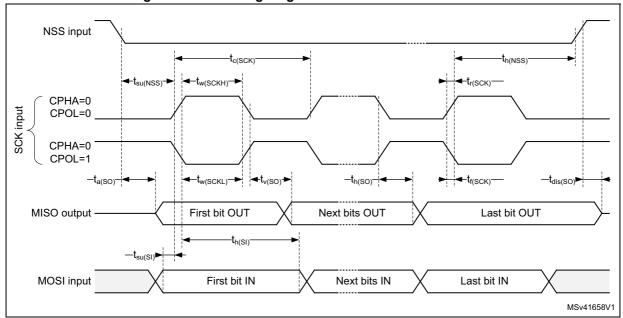
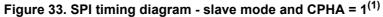
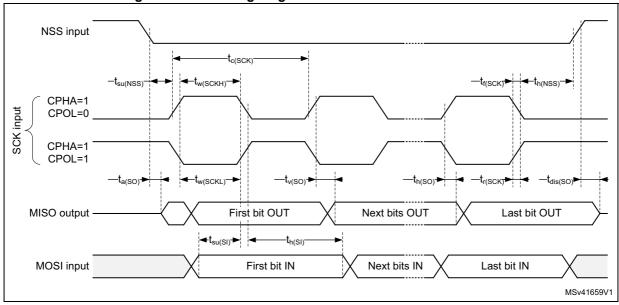


Figure 32. SPI timing diagram - slave mode and CPHA = 0





1. Measurement points are done at CMOS levels: $0.3V_{DD}$ and $0.7V_{DD}$.

Table 78. Standard WLCSP36 - 2.61 x 2.88 mm, 0.4 mm pitch wafer level chip scale mechanical data (continued)

Symbol		millimeters			inches ⁽¹⁾	
Symbol	Min	Тур	Max	Min	Тур	Max
F	-	0.305 ⁽³⁾	-	-	0.012	-
G	-	0.440 ⁽³⁾	-	-	0.017	-
aaa	-	-	0.100	-	-	0.004
bbb	-	-	0.100	-	-	0.004
ccc	-	-	0.100	-	-	0.004
ddd	-	-	0.050	-	-	0.002
eee	-	-	0.050	-	-	0.002

- 1. Values in inches are converted from mm and rounded to the 3rd decimal place.
- 2. Nominal dimension rounded to the 3rd decimal place results from process capability.
- 3. Calculated dimensions are rounded to the 3rd decimal place.

Figure 47. Standard WLCSP36 - 2.61 x 2.88 mm, 0.4 mm pitch wafer level chip scale recommended footprint

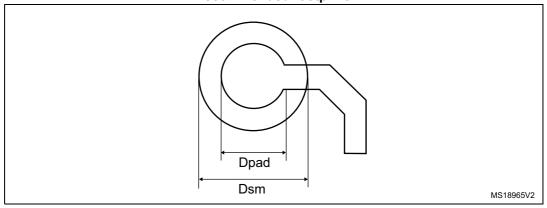


Table 79. Standard WLCSP36 recommended PCB design rules

Dimension	Recommended values
Pitch	0.4 mm
Dpad	260 µm max. (circular) 220 µm recommended
Dsm	300 μm min. (for 260 μm diameter pad)
PCB pad design	Non-solder mask defined via underbump allowed



9 Revision history

Table 86. Document revision history

Date	Revision	Changes
13-Feb-2014	1	Initial release.
29-Apr-2014	2	Added WLCSP36 package. Updated Table 2: Ultra-low-power STM32L051x6/x8 device features and peripheral counts Updated Table 5: Functionalities depending on the working mode (from Run/active down to standby). Added Section 3.2: Interconnect matrix. Updated Figure 4: STM32L051x6/8 TFBGA64 ballout - 5x 5 mm Replaced TTa I/O structure by TC, updated PA0/4/5, PC5/14, BOOT0 and NRST I/O structure in Table 15: STM32L051x6/8 pin definitions. Updated Table 23: General operating conditions, Table 20: Voltage characteristics and Table 21: Current characteristics. Modified conditions in Table 26: Embedded internal reference voltage. Updated Table 27: Current consumption in Run mode, code with data processing running from Flash, Table 29: Current consumption in Run mode, code with data processing running from RAM, Table 31: Current consumption in Sleep mode, Table 32: Current consumption in Low-power run mode, Table 33: Current consumption in Low-power run mode, Table 33: Current consumption in Low-power sleep mode, Table 35: Typical and maximum current consumptions in Stop mode and Table 35: Typical and maximum current consumptions in Standby mode. Added Figure 14: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSE, 1WS, Figure 15: IDD vs VDD, at TA= 25/55/85/105 °C, Run mode, code running from Flash memory, Range 2, HSE, 1WS, Figure 15: IDD vs VDD, at TA= 25/55/85/105/125 °C, Low-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS, Figure 17: IDD vs VDD, at TA= 25/55/85/105/125 °C, Cotop-power run mode, code running from RAM, Range 3, MSI (Range 0) at 64 KHz, 0 WS, Figure 17: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC enabled and running on LSE Low drive and Figure 18: IDD vs VDD, at TA= 25/55/85/105/125 °C, Stop mode with RTC disabled, all clocks OFF. Updated Table 42: HSE oscillator characteristics and Table 43: LSE oscillator characteristics. Added Figure 24: VIH/VIL versus VDD (CMOS I/Os) and Figure 25: VIH/VIL versus VDD (CMOS I/Os) and

